



**PRODUCT NAME :** 2N5321 NPN Small Signal Transistor (Pack of 5)

**PRICE :** Rs 20.00

**SKU :** RM2090



## DESCRIPTION

WITH THE PRODUCT BEING REFERENCED ABOVE. Copyrights by Robomart.com

## Features

- Collector-Emitter Volt ( $V_{ce0}$ ): 50V
- Collector-Base Volt ( $V_{cbo}$ ): 75V
- Collector Current ( $I_c$ ): 1.2A
- $h_{fe}$ : 40-250 @ 500mA
- Power Dissipation ( $P_{tot}$ ): 1000mW
- Current-Gain-Bandwidth ( $f_{total}$ ): 50MHz
- Type: NPN



**2N5320**  
**2N5321**

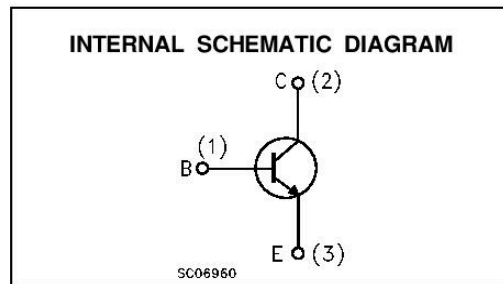
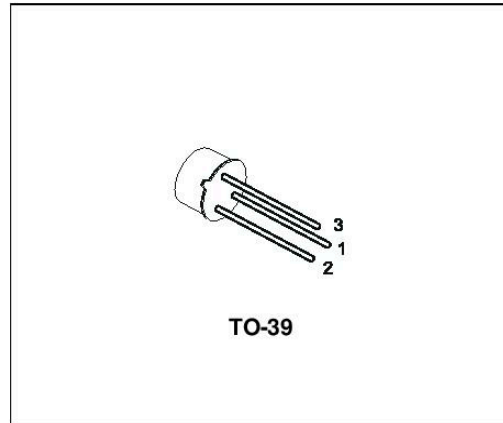
## SMALL SIGNAL NPN TRANSISTORS

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MEDIUM POWER AMPLIFIER
- PNP COMPLEMENTS ARE 2N5322 AND 2N5323

### DESCRIPTION

The 2N5320 and 2N5321 are silicon epitaxial planar NPN transistors in Jedec TO-39 metal case. They are especially intended for high-voltage medium power application in industrial and commercial equipments.

The complementary PNP types are respectively the 2N5322 and 2N5323



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		2N5320	2N5321	
V <sub>CB0</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	100	75	V
V <sub>CEV</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = 1.5V)	100	75	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	75	50	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)	6	5	V
I <sub>C</sub>	Collector Current	1.2		A
I <sub>CM</sub>	Collector Peak Current	2		A
I <sub>B</sub>	Base Current	1		A
P <sub>tot</sub>	Total Dissipation at T <sub>amb</sub> = 25 °C	1		W
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	10		W
T <sub>stg</sub> , T <sub>j</sub>	Storage and Junction Temperature	-65 to 200		°C

**2N5320/2N5321**

**THERMAL DATA**

R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	17.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	175	°C/W

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 80 V for <b>2N5320</b> V <sub>CB</sub> = 60 V for <b>2N5321</b>			0.5 5	μA μA
I <sub>EBO</sub>	Collector Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V for <b>2N5320</b> V <sub>EB</sub> = 4 V for <b>2N5321</b>		0.1 0.5		μA μA
V <sub>(BR)CEV</sub>	Collector-Emitter Breakdown Voltage (V <sub>BE</sub> = 1.5V)	I <sub>C</sub> = 100 μA for <b>2N5320</b> for <b>2N5321</b>	100 75			V V
V <sub>(BR)CEO*</sub>	Collector-Emitter Breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA for <b>2N5320</b> for <b>2N5321</b>	75 50			V V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 100 μA for <b>2N5320</b> for <b>2N5321</b>	6 5			V V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500 mA I <sub>B</sub> = 50 mA for <b>2N5320</b> for <b>2N5321</b>			0.5 0.8	V V
V <sub>BE*</sub>	Base-Emitter Voltage	I <sub>C</sub> = 500 mA V <sub>CE</sub> = 4 V for <b>2N5320</b> for <b>2N5321</b>			1.1 1.4	V V
h <sub>FE*</sub>	DC Current Gain	for <b>2N5320</b> I <sub>C</sub> = 500 mA V <sub>CE</sub> = 4 V I <sub>C</sub> = 1 A V <sub>CE</sub> = 2 V for <b>2N5321</b> I <sub>C</sub> = 500 mA V <sub>CE</sub> = 4 V	30 10 40		130 250	
f <sub>T</sub>	Transition Frequency	I <sub>C</sub> = 50 mA V <sub>CE</sub> = 4 V f = 10 MHz	50			MHz
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 500 mA V <sub>CC</sub> = 30 V I <sub>B1</sub> = 50 mA			80	ns
t <sub>off</sub>	Turn-off Time	I <sub>C</sub> = 500 mA V <sub>CC</sub> = 30 V I <sub>B1</sub> = -I <sub>B2</sub> = 50 mA			800	ns

\* Pulsed: Pulse duration = 300 μs, duty cycle = 1 %

